METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE, SUBSTRATE PROCESSING APPARATUS, AND PROGRAM

ABSTRACT

There is provided a technique, which includes: (a) supplying a modifying agent to a substrate including a first surface and a second surface to form an inhibitor layer on the first surface and at least a portion of the second surface; and (b) forming a film on the second surface by performing a cycle a predetermined number of times, the cycle including (b1) supplying a precursor to the substrate and (b2) supplying a reactant to the substrate, wherein in (b), a process condition per cycle up to an n-th cycle is set to be different from a process condition per cycle on and after an (n+1)-th cycle, wherein n is an integer of 1 or 2 or more.

FIG. 4